

1. Scope
- The present specifications shall apply to an SJPZ-K28.
2. Outline

Type	Silicon Diode
Structure	Resin Molded
Applications	Over Voltage Absorption

3. Flammability
- UL94V-0 (Equivalent)

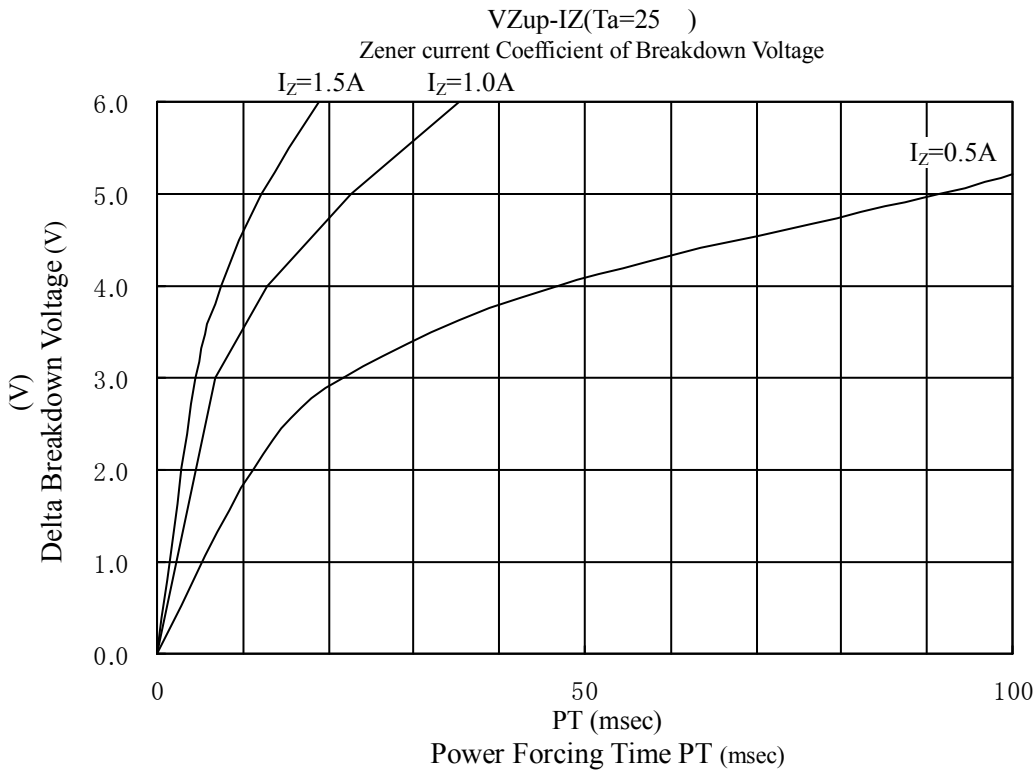
4. Absolute maximum ratings

No.	Item	記号 Symbol	単位 Unit	定 格 Rating	条 件 Conditions
1	Transient Peak Reverse Power	P_R	W	50	Single Square Wave
2	Direct Current Reverse Voltage	V_{RM}	V	20	
3	Permissible Power loss	P	W	1.8 (Ceramic substrate) 1.0 (Glass-Epoxy substrate)	Refer to Derating of 7
4	Peak Surge Reverse Current	I_{ZSM}	A	2	
5	Junction Temperature	T_j	°C	-40~+150	
6	Storage Temperature	T_{stg}	°C	-40~+150	

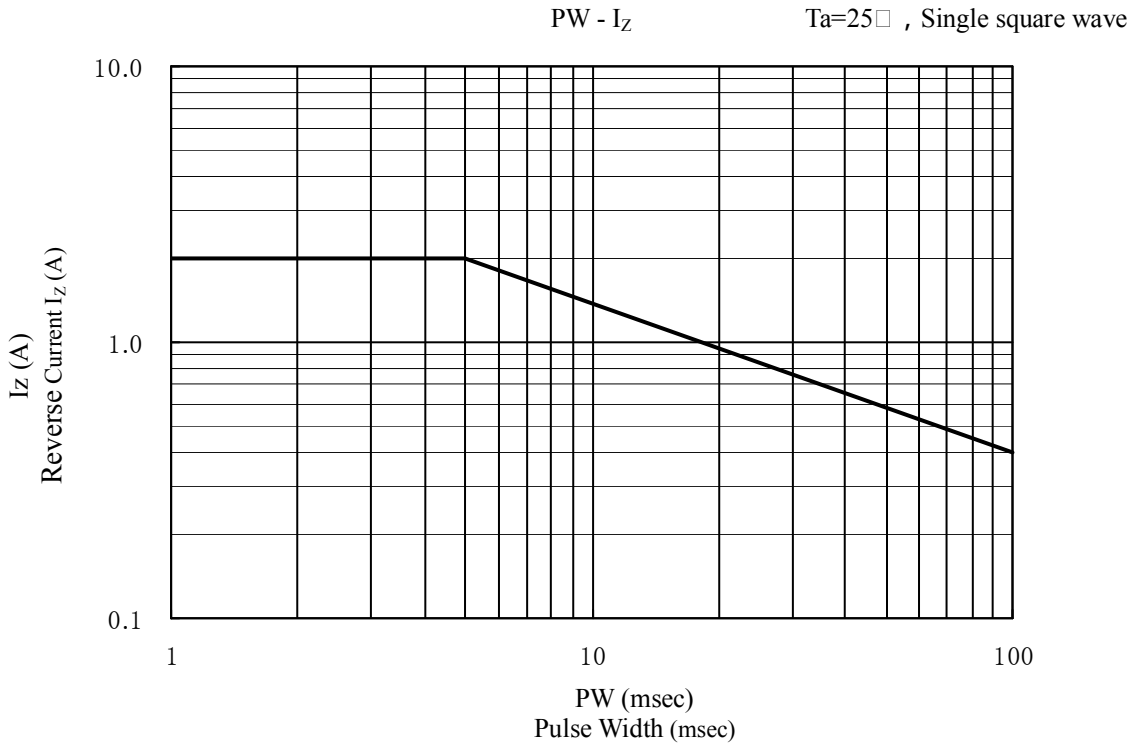
5. Electrical characteristics($T_a=25^{\circ}\text{C}$, unless otherwise specified)

No.	Item	Symbol	Unit	Value	Conditions
1	Forward Voltage Drop	V_F	V	0.95 max.	$I_F=1.0\text{A}$
2	Reverse Brakedown Voltage	V_Z	V	28 ± 3	$I_Z=1\text{mA}$
3	Reverse Leakage Current	I_R	μA	10 max.	$V_R=20\text{V}$
4	Reverse Leakage Current Under High Temperature	$H \cdot I_R$	mA	1.0 max.	$V_R=20\text{V}$, $T_j=150^{\circ}\text{C}$
5	Temperature Coefficient of Breakdown Voltage	γ_Z	$\text{mV}/^{\circ}\text{C}$	25 typ.	$I_Z=1\text{mA}$
6	Equivalent Resistance of Breakdown Region	R_Z	Ω	26 typ.	$I_Z=1\text{mA}$ to 10mA

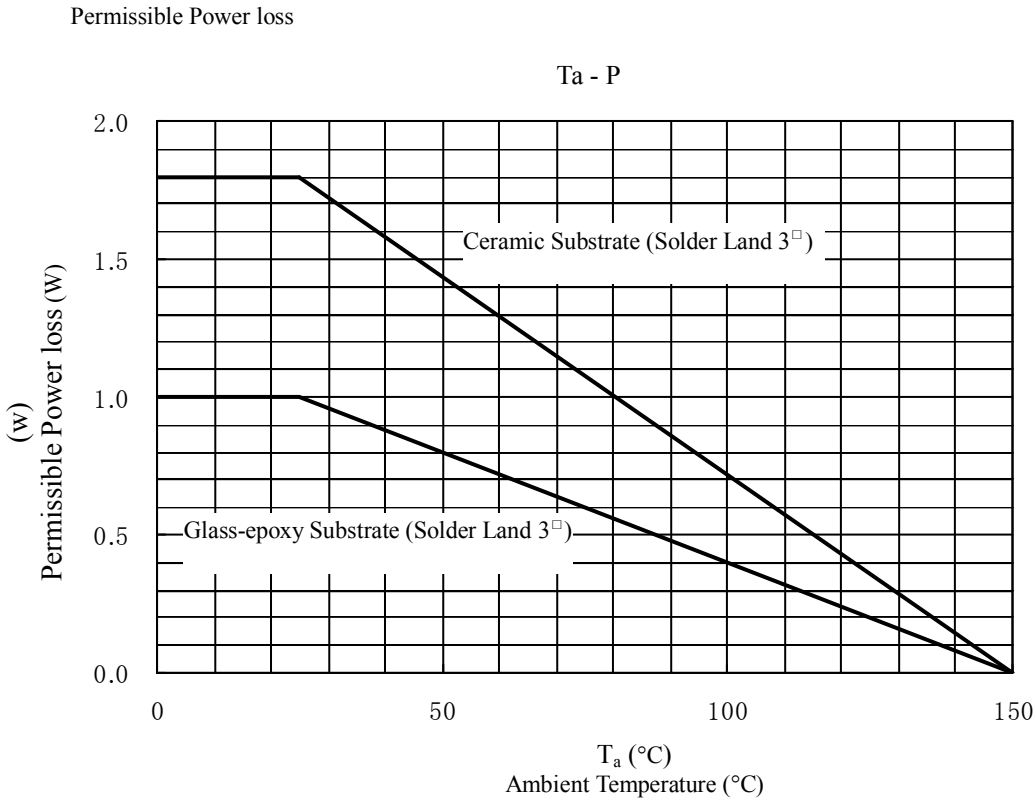
6. Characteristics



Reverse Current

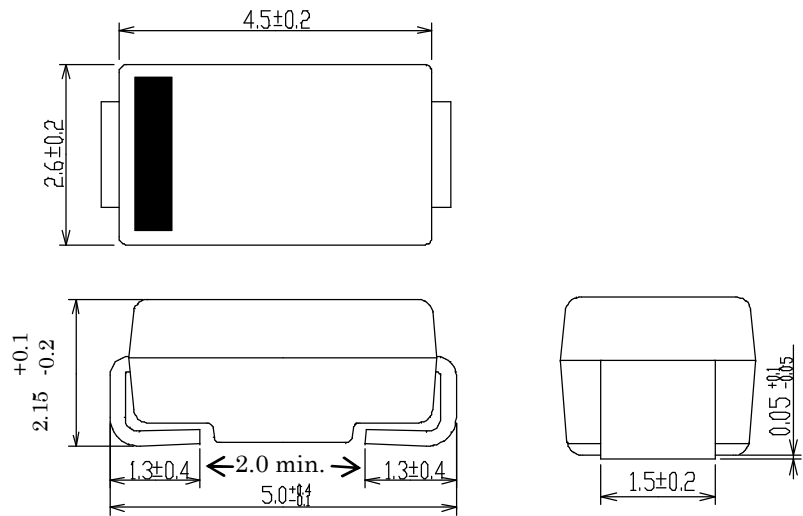


7. Derating



8. Package information

8-1 Package type, physical dimensions

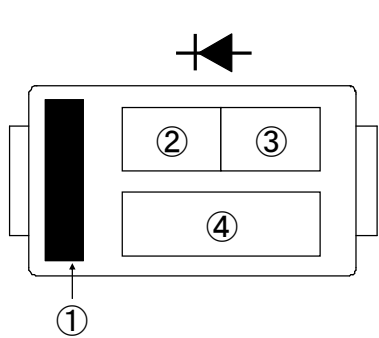


単位 : mm
Dimensions in mm

8-2 Appearance

The body shall be clean and shall not bear any stain, rust or flaw.

8-3 Marking



- 1 Polarity marking (Cathode band)
- 2 Type number
SJPZ-K as abbreviated of ZK.
- 3 Vz Class number
28V as abbreviated of 28.
- 4 Lot number
Example) 6508
6: Last number of Year
5: Month from 1 to 9 for Jan. to Sep. O for Oct. , N for Nov. , D for Dec.
08: Day.

